

Abstract Submitted  
for the MAR11 Meeting of  
The American Physical Society

**Electron Phonon Coupling Mechanism in Thermally Reduced Graphene** MUGE ACIK, GEUNSIK LEE, CECILIA MATTEVI, MANISH CHHOWALLA, KYEONGJAE CHO, YVES J. CHABAL, THE UNIVERSITY OF TEXAS AT DALLAS COLLABORATION, RUTGERS UNIVERSITY COLLABORATION — Infrared absorption of atomic and molecular vibrations in solids can be affected by electronic contributions through non-adiabatic interactions, such as the Fano effect. Typically, the IR absorption lineshapes are modified or IR forbidden modes are detectable as a modulation of the electronic absorption. In contrast to such known phenomena, we report here the observation of a giant IR absorption band in reduced graphene oxide (GO), arising from the coupling of electronic states to the asymmetric stretch mode of a yet unreported structure [1], consisting of oxygen atoms aggregated at edges of defects. DFT calculations show that free electrons are induced by the displacement of the oxygen atoms, leading to a strong IR absorption that is in-phase with the phonon mode. This new phenomenon is only possible when all other oxygen-containing chemical species including hydroxyl, carboxyl, epoxide and ketonic functional groups are removed from the region adjacent to the edges, i.e. clean graphene patches are present. \*The authors acknowledge funding from the NRI SWAN program and Texas Instruments. [1] Acik, M.; Lee, G.; Mattevi, C.; Chhowalla, M.; Cho, K.; Chabal, Y. J. *Nature Materials*. **9**, 840-845 (2010)

Yves J. Chabal  
University of Texas at Dallas

Date submitted: 11 Nov 2010

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